

AD-A231 171

REPORT DOCUMENT			
1a REPORT SECURITY CLASSIFICATION Unclassified		1b RI	
2a SECURITY CLASSIFICATION AUTHORITY JAN 18 1991		3 DISTRIBUTION/AVAILABILITY OF REPORT Approved for public release; distribution unlimited.	
2b DECLASSIFICATION/DOWNGRADING SCHEDULE B		4 PERFORMING ORGANIZATION REPORT NUMBER(S)	
5a NAME OF PERFORMING ORGANIZATION Stanford University		5b OFFICE SYMBOL (If applicable)	
6a ADDRESS (City, State, and ZIP Code) AEL 202 Stanford, CA 94305-4055		7a NAME OF MONITORING ORGANIZATION U. S. Army Research Office	
6b ADDRESS (City, State, and ZIP Code) P. O. Box 12211 Research Triangle Park, NC 27709-2211		7b ADDRESS (City, State, and ZIP Code) P. O. Box 12211 Research Triangle Park, NC 27709-2211	
8a NAME OF FUNDING/SPONSORING ORGANIZATION U. S. Army Research Office		8b OFFICE SYMBOL (If applicable)	
9 PROCUREMENT INSTRUMENT IDENTIFICATION NUMBER DAAL03-87-K-0077		10 SOURCE OF FUNDING NUMBERS	
PROGRAM ELEMENT NO		PROJECT NO	TASK NO
WORK UNIT ACCESSION NO			
11 TITLE (Include Security Classification) Computer Aided Design Tools and Algorithms for Submicron Technologies			
12 PERSONAL AUTHOR(S) Robert W. Dutton			
13a TYPE OF REPORT Final Report		13b TIME COVERED FROM 7-1-87 TO 6-30-90	
14 DATE OF REPORT (Year, Month, Day) October 23, 1990		15 PAGE COUNT	
16 SUPPLEMENTARY NOTATION The view, opinions and/or findings contained in this report are those of the author(s) and should not be construed as an official Department of the Army position, policy, or decision, unless so designated by other documentation.			
17 COSATI CODES		18 SUBJECT TERMS (Continue on reverse if necessary and identify by block number)	
FIELD	GROUP	SUB-GROUP	
		Mixed-mode simulation, Monte Carlo, two-dimensional, three-dimensional, device analysis, parallel processing, distributed multifrontal, Intel hypercube, MOS, BiCMOS, GaAs, (over)	
19 ABSTRACT (Continue on reverse if necessary and identify by block number) Advanced algorithms for two- and three-dimensional modeling of semiconductor devices have been developed, implemented on parallel computers and tested using several high performance technologies. Computational limitations for semiconductor device analysis have been extended to greater than $10^5$ nodes and speedup factors greater than 10-fold have been realized using distributed memory (MIMD) architectures. Two classes of algorithms have been explored using parallel processing--distributed multifrontal (DMF) and Monte Carlo (MC). The DMF algorithm has been implemented and tested for 3D device analysis of MOS, bipolar and latchup examples using iterative methods for single- and two-carrier transport. A windowed MC analysis of 2D hot carrier effects in Si MOS and GaAs MESFET devices has been achieved on several parallel architectures with near ideal speedup factors up to 20 processors.  Usability of device simulation has been enhanced and demonstrated through applications. The range of technologies that can be modeled with the 2D PISCES program now includes: GaAs, GeSi heterojunctions and photo- and other carrier-generation processes. Moreover, layout-driven input and 2D/3D output visualization capabilities increase user efficiency. Device and technology scaling applications have been used to evaluate both 2D and 3D device capabilities. BiCMOS scaling issues and new structures have been evaluated using PISCES and mixed-mode (device/circuit) capabilities. Broad use of this work both in industry and government has been demonstrated. The 3D prototype code STRIDE has been used to analyze CMOS latchup. Industrial interest in this code has resulted in State of California support to move the prototype into commercial development.			
20 DISTRIBUTION/AVAILABILITY OF ABSTRACT <input type="checkbox"/> UNCLASSIFIED/UNLIMITED <input type="checkbox"/> SAME AS RPT <input type="checkbox"/> DTIC USERS		21 ABSTRACT SECURITY CLASSIFICATION Unclassified	
22a NAME OF RESPONSIBLE INDIVIDUAL		22b TELEPHONE (Include Area Code)	22c OFFICE SYMBOL

UNCLASSIFIED

SECURITY CLASSIFICATION OF THIS PAGE

Block 18 cont.

heterojunction bipolar, GeSi technology scaling, latchup, transient behavior, PISCES, STRIDE, photoconductivity, picosecond optical switching hot carriers.

UNCLASSIFIED

SECURITY CLASSIFICATION OF THIS PAGE

**COMPUTER AIDED DESIGN TOOLS AND  
ALGORITHMS FOR SUBMICRON TECHNOLOGIES**

**Final Report**

by

**Robert W. Dutton  
Stanford University  
Stanford, CA 94305**

**July 1, 1987--June 30, 1990**

**Prepared for**

**U. S. Army Research Office  
Research Triangle Park, NC**

**Contract No. DAAL03-87-K-0077**

**Approved for public release; distribution unlimited**

# COMPUTER AIDED DESIGN TOOLS AND ALGORITHMS FOR SUBMICRON TECHNOLOGIES

Robert W. Dutton  
Stanford University  
Stanford, CA 94306

## Abstract

Advanced algorithms for two- and three-dimensional modeling of semiconductor devices have been developed, implemented on parallel computers and tested using several high performance technologies. Computational limitations for semiconductor device analysis have been extended to greater than  $10^5$  nodes and speedup factors greater than 10-fold have been realized using distributed memory (MIMD) architectures. Two classes of algorithms have been explored using parallel processing--distributed multifrontal (DMF) and Monte Carlo (MC). The DMF algorithm has been implemented and tested for 3D device analysis of MOS, bipolar and latchup examples using iterative methods for single- and two-carrier transport. A windowed MC analysis of 2D hot carrier effects in Si MOS and GaAs MESFET devices has been achieved on several parallel architectures with near ideal speedup factors for up to 20 processors.

Usability of device simulation has been enhanced and demonstrated through applications. The range of technologies that can be modeled with the 2D PISCES program now includes: GaAs, GeSi heterojunctions and photo- and other carrier-generation processes. Moreover, layout-driven input and 2D/3D output visualization capabilities increase user efficiency. Device and technology scaling applications have been used to evaluate both 2D and 3D device capabilities. BiCMOS scaling issues and new structures have been evaluated using PISCES and mixed-mode (device/circuit) capabilities. Broad use of this work both in industry and government has been demonstrated. The 3D prototype code STRIDE has been used to analyze CMOS latchup. Industrial interest in this code has resulted in State of California support to move the prototype into commercial development.

Accession For	
NTIS GRA&I	<input checked="" type="checkbox"/>
DTIC TAB	<input type="checkbox"/>
Unannounced	<input type="checkbox"/>
Justification	
By	
Distribution/	
Availability Codes	
Avail and/or	
Special	

1st  
A-1



## Introduction

New analysis tools and techniques for technology scaling are essential for higher speed applications. Scaling device dimensions also causes reliability problems such as hot carrier effects. This research effort focuses on achieving faster and larger-scale analysis capabilities for semiconductor devices based on the use of parallel computers. In order to demonstrate the utility of these new techniques, a variety of applications are demonstrated. Over the course of this project four PhD's have graduated and a number of industrial and government interactions have facilitated technology transfer. The following sections summarize accomplishments in algorithms, device analysis, and applications.

## Algorithms

The analysis of semiconductor devices over the past two decades has been driven by the so-called drift/diffusion formulation of the carrier continuity equations. The growing importance of hot carrier effects necessitates that higher moments of the Boltzmann transport equation (BTE) are needed to determine carrier temperature distributions. Two approaches have become popular: 1) coupled solution of addition momentum and energy equations, 2) direct solution of the BTE using Monte Carlo (MC) techniques. The energy balance approach has the advantages of computational speed and direct extension of the partial differential equations (PDE's) used for drift/diffusion. The Monte Carlo approach allows more accurate first-principles modeling of the carrier motion; the major disadvantage comes from requirements for analysis of many particles in the time domain. In this research the MC analysis approach was chosen to augment the drift/diffusion formulation based on two key factors: 1) that parallel processing can reduce CPU requirements by several orders of magnitude and 2) that "windowing" the analysis region can also affect requirements on number of particles and computation times. Progress in both these aspects is reported.

While MC techniques are proving to be more practical for device analysis based on the parallel computation techniques described above, the solution of PDE's on a discretized 2D or 3D grid still provides the work horse of technology analysis. While the choice of which PDE's (drift/diffusion or an augmented energy balance formulation) is still an open issue, the need for more efficient solvers is fundamental to the broad engineering application. In this research program a parallel implementation of distributed multifrontal (DMF) assembly and solver algorithms has been realized on both distributed (hypercube) and shared memory (Cray and Convex) multiprocessor architectures. Moreover, these algorithms have been used in the prototype 3D device analysis program "STRIDE" which has been tested for MOS, bipolar and latch-up simulations. Progress on both solvers and implementation for device analysis are now outlined.

A new distributed multifrontal algorithm for solving large sparse systems of equations has been developed that overcomes the communication bottleneck previously reported for general sparse solvers. An order of magnitude reduction in the communication load has been demonstrated for a sample problem. Using this new technique, parallel processor efficiencies of 70 percent have been observed using an Intel iPSC with 16 processors [1]. This level of efficiency was observed over both a range of problems and a varying number of processors. While this algorithm was originally intended for use on a distributed memory hypercube, it has been demonstrated to be applicable to shared memory systems; for shared memory system the communication overheads manifest themselves as synchronization and mutual exclusion problems [2].

The communication overhead is minimized by a frontal distribution of physically adjacent pivots' rows and columns to one processor. Separate blocks can be factored without interprocessor communication since updates to their separator fronts are stored locally. Message traffic is also restricted while factoring the separator submatrices. During the dissection process, the blocks of the dissected problem are always divided between logically adjacent processors. Therefore, the set of processors factoring any separator's submatrix is always a complete hypercube of lower dimension (i.e. subcube) embedded within the multiprocessor. All messages needed to resolve data dependencies during the separator factorization are transmitted using a spanning tree that is restricted to the subcube. The messages are limited and remain in the working subcube. Even though this work was motivated by semiconductor device simulation, the sparse matrix solution technique is applicable to a wide range of scientific and engineering disciplines. This work was focused on rectangular grids. However, automatic nested dissection routines can be used to extend the usefulness of the DMF algorithm to problems generated from irregular 2-D grids.

A 3-D one carrier device solver has been developed using DMF on an Intel iPSC2 hypercube multiprocessor capable of handling over 130K nodes. CPU times of 20 minutes per bias point on a 50K node MOSFET example [3] [4] have been demonstrated. Slotboom variables are used in conjunction with the Scharfetter-Gummel current discretization scheme. A scaling scheme was implemented which produces,  $n$  and  $p$  variables from the Slotboom variables. An improved damped-Newton scheme, which maintains the iteration numbers at below fifteen for high gate biases, is used in solving Poisson's equation. The performance of an initial guess scheme developed in this work is improved through the use of a novel update strategy during the Poisson solution stage after the initial guess step. This improvement allows stable calculation for voltage steps as high as five volts. A modified singular perturbation scheme (MSP) has been proposed whose implementation speeds up the convergence under high  $V_{gs}$  and  $V_{ds}$  bias conditions by a factor of three to six times. A block matrix analysis of the MSP scheme yields insight into its performance [4][5].

In the area of Monte Carlo analysis, a new multiwindow multimethod device analysis algorithm which combines the advantages of efficient drift-diffusion simulators and accurate physical models using MC methods has been demonstrated [6]. The PISCES 2-D device analysis program is used whenever the drift-diffusion model is valid. In situations where the drift-diffusion model breaks down, a window is opened in the part of the device where the hot carrier effects are important. The Monte Carlo method in the McPOP program is then applied in the window. The simulation results obtained match well with the measured data and the full Monte Carlo results. The CPU time required has been reduced by a factor of 3 to 10 compared with the full Monte Carlo simulation. A parallel Monte Carlo algorithms has been used in the McPOP program. A 20 processor system speeds up the program by a factor of 18.5. To our knowledge, this is the first parallel Monte Carlo device analysis program.

The PISCES-MC program is composed of two parts, a drift-diffusion model-based solver in the PISCES program, and a multiparticle Monte Carlo solver in the McPOP (Portable Parallel Monte Carlo) program. A window is used to connect these two parts together. In the McPOP program, a direct-method-based Poisson solver is used to find the electric field, and the Monte Carlo method is used to find an indirect solution to the Boltzmann transport equation.

Three criteria are used to place the window boundaries in a device. First, at a window boundary, the spatial derivatives of the electric field are low and the values of the electric field must be smaller than the threshold field. Second, the total carrier velocity at a window boundary must be smaller than the saturation velocity. Third, the number of the carriers in the upper conduction band at a window boundary must be negligible. These criteria ensure that the drift-diffusion-based simulator gives an accurate solution at the window boundaries, and that the velocity distribution is a displaced Maxwellian at these locations. Figure 1 shows the connection of the two programs and how they interact.

In order to reduce the CPU time required to a practical range, the McPOP program uses a parallel Monte Carlo algorithm. Parallel programs have in the past been notoriously machine specific. Nonportability has been one of the main factors of the high development cost of parallel software. The new program addresses this problem by using a portable concurrency package. The McPOP program was developed and debugged on a Convex-C1 system using UNIX multitasking facilities. It has been ported to the SEQUENT Balance 8000 and the ALLIANT FX/8, and only recompilation is required to run this program on a new parallel machine with the UNIX operating system and shared memory.

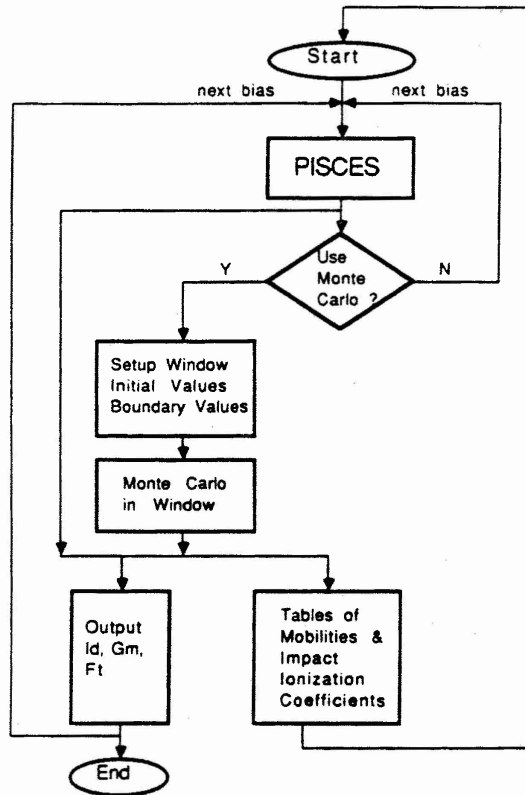


Figure 1: Flow chart of the PISCES-MC program

## Device Analysis

Availability of efficient and robust solvers is one essential component for semiconductor device analysis. However, without implementation and testing of physically correct materials parameters and transport equations, device analysis is not possible. Over the course of this research project the base of physical models has been dramatically enhanced. Based on the reduced funding for this project, aspects of this physical modeling work were sustained under other research programs. Specifically, silicon modeling support from the Semiconductor Research Corporation (SRC) was essential to this project. The range of silicon models implemented and tested over this contract period included: improved MOS and bipolar mobility models and generation processes--both from photo and avalanche processes.

Models for GaAs were implemented both for the Monte Carlo and drift/diffusion analysis capabilities. For the PDE-based analysis in PISCES, major enhancements include: trap modeling and improved implementation of mobility models with supporting nonlinear update procedures. Over the course of this contract the support for GaAs modeling has been sporadic. Initially SRC funded PISCES work but this ended within the first year of the ARO contract. Over the last two years DARPA has funded limited device analysis work related to testing of the process modeling (SUPREM 3.5) capabilities which is their primary area of interest. The aggregate support for GaAs modeling was sufficient to realize a major advance in MESFET analysis capabilities over this contract period. However, due to the relative immaturity of these enhancements and the projected July 1991 end of DARPA support, it is appropriate to conclude that further follow-on work in this area should be considered.

Two unique aspects of the enhanced analysis capabilities developed under this contract are multilayer modeling and radiation-induced carrier generation. Both of these activities have been motivated by interests from the IR detector community. In particular the needs of the ManTech program supported through the Air Force provided initial coupling and more recently the Army's Strategic Defense Command in Huntsville is now continuing to make use of this modeling effort. Hughes/SBRC (Santa Barbara Research Corporation) has in fact used PISCES prototypes as key components in developing the SABRE package being developed for HCT IR detector analysis. The activities specifically supported under this contract have used different materials systems and applications to drive the device analysis capabilities. For the heterojunction work, the present implementation has been targeted to support GeSi heterojunction bipolar device analysis [7]. In the case of radiation-induced carrier generation, the target is transient analysis of photoconductors using polycrystalline GaAs on silicon [8] [9]. We anticipate follow-on activities and collaboration with Hughes/SBRC for the IR applications.

## Applications

The above section briefly outlined applications of device analysis in several areas key to DoD needs--high speed GaAs and IR detectors based on HCT technology. Moreover, the connection of silicon research efforts supported under SRC have been indicated. In this section special attention is given to the areas of BiCMOS scaling, latchup analysis and a new framework for application of device analysis.

The analysis of latchup is a theme that has sustained considerable interest for more than a decade, owing to its serious impact on CMOS circuits. During an earlier contract one PhD was graduated, achieving major research contributions in analytical formulations for latchup analysis [10]. During this contract period a second PhD was graduated, in this case making new



contributions in numerical techniques [11]. The key points of this work are based on the development of robust algorithms for 2D device simulation and control of its analysis under the conditions of latchup. Specifically, new gridding capabilities based on both technology constraints and numerical accuracy have been implemented and tested. In the area of tracing out the complex I-V curves observed for latch up structures, a new continuation method was developed. The above accomplishments thereby allow a robust and efficient numerical analysis of latchup. These features are now being implemented in the PISCES code based on the prototype work reported above [11].

The rapid emergence of BiCMOS as technology suitable for both high speed digital and mixed analog/digital applications has stimulated broad interest among the design community. Yet the trade-offs in technology choices for different circuit applications have been elusive. In this work two major thrusts in BiCMOS analysis have yielded insightful design information.

The effects of different MOS and bipolar device parameters on the switching speed of BiCMOS buffers have been examined. The switching speed is studied by looking at the pull-up transient for a step input. Mathematical approximations are derived for two cases of bipolar high collector current behavior and compared with SPICE and mixed-mode simulations [12] [13]. The total parasitic capacitance at the base has a small effect on the delay time. More important are the parameters  $\tau_f$ , which models the charge storage in the base, and  $I_k$ , which models the high-current effects. A high  $I_k$  and low  $\tau_f$  provide the highest speeds. Based on these results an investigation of scaling issues was carried out [14]. Scaling rules for bipolar transistors for BiCMOS drivers were derived such that the BiCMOS gate maintains its advantage over the CMOS gate for driving large load capacitors. These scaling rules were compared with the scaling rules for bipolar transistors for ECL circuits. While the trends are similar, there is a conflict in the requirement for the collector profile. Bipolar transistors for BiCMOS drivers require a high collector doping concentration (typically higher than  $5 \times 10^{16} \text{ 1/cm}^3$  while ECL circuits require bipolar transistors with lower value for the collector doping concentration (typically lower than  $2 \times 10^{16} \text{ 1/cm}^3$ ). As a follow-on to this effort, collaboration with HP, IBM and Stanford's CIS is targeted to realize practical BiCMOS devices to prove experimentally these conclusions.

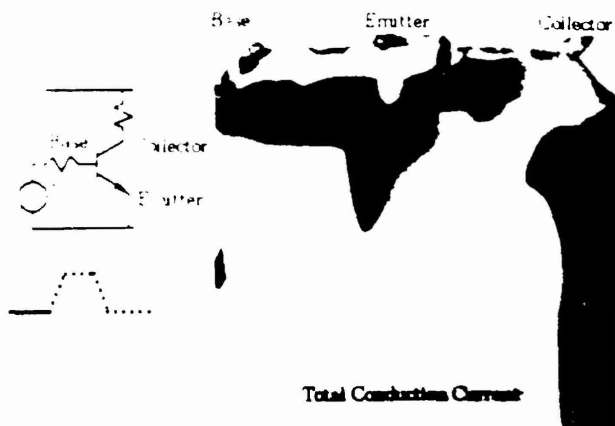
A final aspect of the BiCMOS effort has been the realization of test circuits based in insight gained through this research effort. In collaboration with staff members at Signetics, novel test circuits were designed and tested for realizing high speed sense circuits under conditions of heavy capacitance loading [15]. The trade-offs of various BiCMOS configurations were evaluated and unique sense circuits were realized experimentally. The bipolar transistors in BiCMOS technology have typically been used to drive large capacitors. An alternative approach is to reduce the voltage swing on the highly capacitive nodes and use subsequent amplification. The basic idea for the sense circuit in this work uses a bipolar transistor used in a common-emitter configuration. This circuit was implemented for two different sets of custom source bias resistors R1 and R2. A 32-bit adder using this circuit was implemented in the same technology. For every 4-bit block, the sum is calculated for both the input carry equal to 1 and the input carry equal to 0.

The previous BiCMOS scaling analysis is indicative of growing demands placed on state of the art Technology CAD. Namely, several levels of design abstraction--circuits devices and

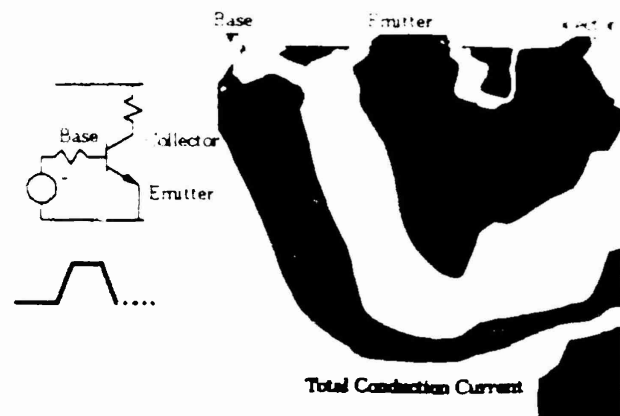
technology--must all be dealt with concurrently. During this contract period, a new thrust has been initiated in the area of TCAD framework tools. This effort has broad connections to both academic and industrial activities. Specifically, the work relates to SRC needs in design sciences and joint efforts with colleagues at UC Berkeley is reported. Also, as indicated in the renewal proposal for this work, there is now a TCAD Framework initiative that this work will directly contribute towards. Accomplishments during this contract are built primarily on the user requirements and supporting data structures of PISCES. Initially a set of automeshing capabilities were implemented to support PISCES [16]. This evolved into support for complete user "stencils" based on the circuit application for the devices and the associated design rules [17]. Most recently in collaboration with UC Berkeley we have integrated PISCES into a framework based on the SIMPL-IPX graphics interface [18]. This system allows the user to edit and select cross-sections for device analysis based on circuit layout. The system also interfaces various process simulation tools such as SUPREM and SAMPLE. The above efforts have illustrated and identified key problems of tool integration that are now becoming part of the TCAD framework standards. It is not the intent of this report to summarize or give details of this framework evolution--it is a process now being acted out between industry and universities. However, it is indeed useful to cite specific accomplishments from this work that have a direct impact on further prototyping. The three points chosen as illustrative are:

1. Grid agents
2. Window management
3. Visualization

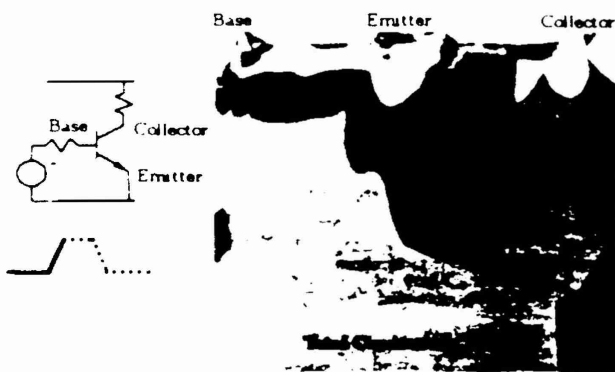
The gridding examples cited above [11][16][17] all show remarkable progress in automation and intelligent user support of device analysis gridding. The next stage is to build on this work and make it possible to interface with a diversity of programs [18] and other fields of importance such as solid modeling. In the area of window management, the evolution from single application windows to a true multi-window system is a key next step. Results to date show excellent progress in that direction [17][18]. The final area of significant progress concerns improved output visualization. The recent results using public domain IMAGE software [19] in concert with improved PISCES application support [17], helps to show the way towards robust multi-window capabilities. Figure 2 gives an excellent example of visualizing PISCES results for a transient switching analysis of a BiCMOS transistor.



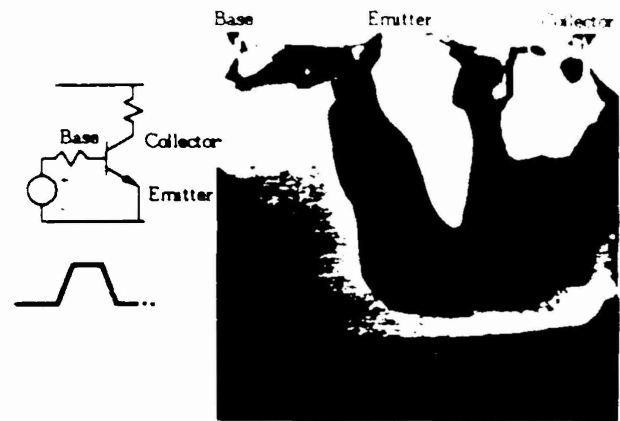
a) Cutoff



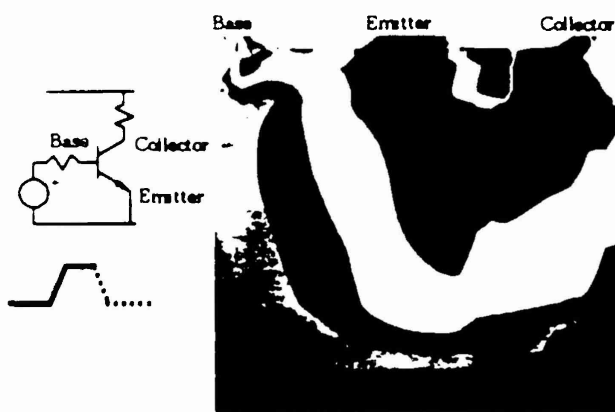
d) Bias Removed



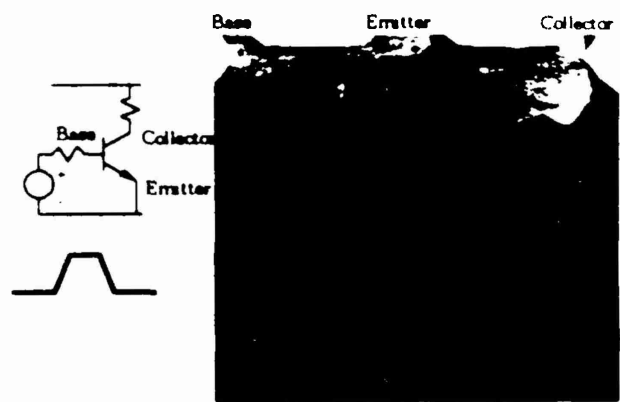
b) Forward Active



e) Base Charge Removed



c) Saturation



f) Cutoff

Figure 2: Frames from Transient Bipolar Simulation

## References

- [1] R. Lucas, T. Blank, J. Tiemann, "A Parallel Solution Method for Large Sparse Systems of Equations, Presented at ICCAD, Santa Clara, CA Nov. 1986.
- [2] S. D. King, R. Lucas, A. Raefsky, "Using a Multifrontal Solver in High Performance Finite Element Software," Submitted to Supercomputer Journal.
- [3] R. F. Lucas, K. C. Wu, and R. W. Dutton, "A Parallel 3-D Poisson Solver on a Hypercube Multiprocessor," Presented at ICCAD, November 9, 1987, Santa Clara, CA.
- [4] K. C. Wu, R. F. Lucas, Z. Y. Wang, and R. W. Dutton, "New Approaches in a Parallel 3-D One-Carrier Device Solver, Presented NUPAD II, San Diego, CA, May 1988.
- [5] K. C. Wu, R. F. Lucas, Z. Y. Wang, and R. W. Dutton, "New Approaches in a 3-D One-Carrier Device Solver," *IEEE Trans. CAD/ICAS*, Vol. 8, No. 5, May 1989.
- [6] D. Y. Cheng, C. G. Hwang, R. W. Dutton, "PISCES-MC, A Multi-window, Multi-Method 2D Device Simulator," *IEEE Trans. CAD/ICAS*, Vol. CAD-7, No. 9, Sept. 1988.
- [7] Z. Yu, P. E. Cottrell, R. W. Dutton, Modeling and Simulation of High-Level Injection Behavior in Double Heterojunction Bipolar Transistors," IEEE 1990 Bipolar Circuits and Technology Meeting,
- [8] J. D. Morse, R. Mariella, G. D. Anderson, and R. W. Dutton, "Picosecond GaAs Photoconductors on Silicon Substrate for Local Integration with Silicon Devices and Circuits," *IEEE Elect. Dev. Lett.*, Vol. 10, No. 1, Jan. 1989.
- [9] J. D. Morse, R. P. Mariella, and R. W. Dutton, "Picosecond Photoconductivity Using a Graded Bandgap  $\text{Al}_x\text{Ga}_{1-x}\text{As}$  Active Detecting Layer," IEDM Technical Digest, Dec. 1989.
- [10] D. B. Estreich, "The Physics and Modeling of Latch-up and CMOS Integrated Circuits," PhD thesis, Stanford University, Nov. 1980.
- [11] M. R. Pinto, "Comprehensive Semiconductor Device Simulation for Silicon ULSI," PhD thesis, Stanford University, Aug. 1990.
- [12] G. P. Rosseel, K. Mayaram, R. W. Dutton, D. O. Pederson, "Delay Analysis of BiCMOS Drivers," Presented *Bipolar Circuits and Technology Meeting*, Sept. 1988.
- [13] G. P. Rosseel, R. W. Dutton, "Influence of Device Parameters on the Switching Speed of BiCMOS Buffers," *IEEE JSSC*, Vol. 24, No. 1, Feb. 1989.

[14] G. Rosseel, R. W. Dutton, "Scaling Rules for Bipolar Transistors in BiCMOS Circuits," IEDM Technical Digest, Dec. 1989.

[15] G. P. Rosseel, M. A. Horowitz, R. L. Cline, and R. W. Dutton, "A Single-ended Sense Circuit for Digital BiCMOS Circuits", 1989 International Solid-State Circuits Conference, New York, Feb. 1989.

[16] G. Chin, R. W. Dutton, "User Interfaces to Device and Process Simulation Tools, " Presented TECHCON 88, Dallas, Texas, October 1988.

[17] G. Anderson, G. Chin, M. Eldredge, A. Raefsky, Z. Yu, and R. Dutton, "Metamorphosis of PISCES - Application-Oriented Transformation of 2D Device Simulation" Presented TECHCON 1990, San Jose, CA, October 15-18, 1990

[18] E. W. Scheckler, A. S. Wong, R. H. Wang, G. Chin, J. R. Camagna, K. K. H. Toh, K. H. Tadros, R. A. Ferguson, A. R. Neureuther, and R. W. Dutton, "A Utility-Based Integrated Process Simulation System", Presented 1990 Symposium on VLSI Technology, Honolulu, Hawaii, June 5-7, 1990.

[19] NCSA Documentation Department, "NCSA XImage for the X Window System, Version 1.0, November 1989.